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May 2014

FCA47N60F — N-Channel SuperFET[®] FRFET[®] MOSFET

FCA47N60F N-Channel SuperFET[®] FRFET[®] MOSFET

600 V, 47 A, 73 m Ω

FAIRCHILD

Features

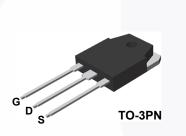
- 650 V @ T_J = 150 °C
- Typ. R_{DS(on)} = 62 mΩ
- Fast Recovery Time (Typ. T_{rr} = 240 ns)
- Ultra Low Gate Charge (Typ. Q_g = 210 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 420 pF)
- 100% Avalanche Tested
- RoHS Compliant

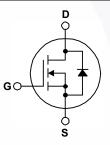
Applications

- Solar Inverter
- AC-DC Power Supply

Description

SuperFET[®] MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. Super-FET FRFET[®] MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FCA47N60F	Unit	
V _{DSS}	Drain-Source Voltage			600	V	
I _D	Drain Current	- Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)		47 29.7	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	141	A	
V _{GSS}	Gate-Source voltage			± 30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	1800	mJ	
I _{AR}	Avalanche Current		(Note 1)	47	A	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	41.7	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	50	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C		417 3.33	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

Thermal Characteristics

Symbol	Parameter	FCA47N60F	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.3	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	41.7	°C/W	

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Part N	umber	Top Mark	Package	Packing Method	Reel Size	Та	pe Width	Qu	antity
FCA4	· · ·		TO-3PN	Tube	N/A		N/A	30 units	
Electric	al Char	acteristics T _c = 25°C u	nless otherwise	noted					
Symbol		Parameter		Conditions			Тур.	Max.	Unit
Off Charac	teristics								
BV _{DSS}	Drain-Source Breakdown Voltage		$V_{GS} = 0$	V_{GS} = 0 V, I_{D} = 250 μ A, T_{J} = 25°C					V
			$V_{GS} = 0$	V_{GS} = 0 V, I _D = 250 µA, T _J = 150°C			650		V
ΔΒV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient $I_D = 250 \mu A$, Refe) μA, Referenced to 2	renced to 25°C				V/°C
BV _{DS}	Drain to Source Avalanche Breakdown V _{GS} = 0 V, I_D = 47 A Voltage					700		v	
I _{DSS}	Zero Gate	Voltage Drain Current		$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V},$ $V_{DS} = 480 \text{ V}, T_{C} = 125^{\circ}\text{C}$				10 100	μΑ μΑ
I _{GSSF}	Gate-Body	/ Leakage Current, Forward	V _{GS} = 3	V _{GS} = 30 V, V _{DS} = 0 V				100	nA
I _{GSSR}	Gate-Body	/ Leakage Current, Reverse	V _{GS} = -	V _{GS} = -30 V, V _{DS} = 0 V				-100	nA
On Charac	teristics						11		1
V _{GS(th)}	Gate Thre	shold Voltage	V _{DS} = V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$				5.0	V
R _{DS(on)}	Static Drai On-Resist		V _{GS} = 1	V _{GS} = 10 V, I _D = 23.5 A			0.062	0.073	Ω
9 _{FS}	Forward T	ransconductance	V _{DS} = 4	V _{DS} = 40 V, I _D = 23.5 A			40		S
Dynamic C	haracterist	tics							
C _{iss}	Input Capa	acitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz			5900	8000	pF
C _{oss}	Output Ca	pacitance	f = 1 Mł				3200	4200	pF
C _{rss}	Reverse T	ransfer Capacitance					250		pF
C _{oss}	Output Ca	pacitance	V _{DS} = 4	V _{DS} = 480 V, V _{GS} = 0 V, f = 1 MHz			160		pF
Coss(eff.)	Effective C	Dutput Capacitance	$V_{DS} = 0$	V_{DS} = 0 V to 400 V, V_{GS} = 0 V			420		pF
Switching	Characteris	stics							
t _{d(on)}	Turn-On D	elay Time		$V_{DD} = 300 \text{ V}, \text{ I}_{D} = 47 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega$ (Note 4)			185	430	ns
t _r	Turn-On R	Rise Time	V _{GS} = 1				210	450	ns
t _{d(off)}	Turn-Off D	elay Time					520	1100	ns
t _f	Turn-Off F	all Time					75	160	ns
Qg	Total Gate	Charge		V _{DS} = 480 V, I _D = 47 A, V _{GS} = 10 V			210	270	nC
Q _{gs}	Gate-Sour	ce Charge	V _{GS} = 1				38		nC
Q _{gd}	Gate-Drain	n Charge		(Note 4)			110		nC
Drain-Sour	ce Diode C	haracteristics and Maxim	um Ratings	3					
I _S	Maximum Continuous Drain-Source Diode Forward Current					47	Α		
I _{SM}	Maximum	Pulsed Drain-Source Diode	Forward Cu	orward Current				141	Α
V _{SD}	Drain-Sou	rce Diode Forward Voltage	$V_{GS} = 0$	V _{GS} = 0 V, I _S = 47 A				1.4	V
t _{rr}	Reverse R	Recovery Time		$V_{GS} = 0 V, I_S = 47 A,$			240		ns
Q _{rr}		Recovery Charge	dl⊧/dt =	100 A/µs	-		2.04		μC

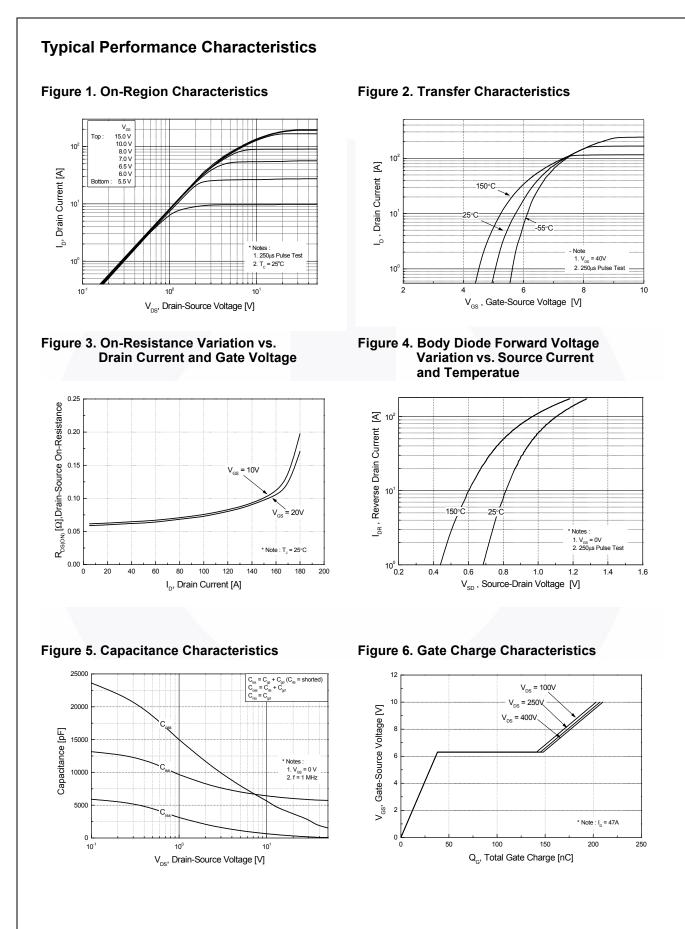
Notes:

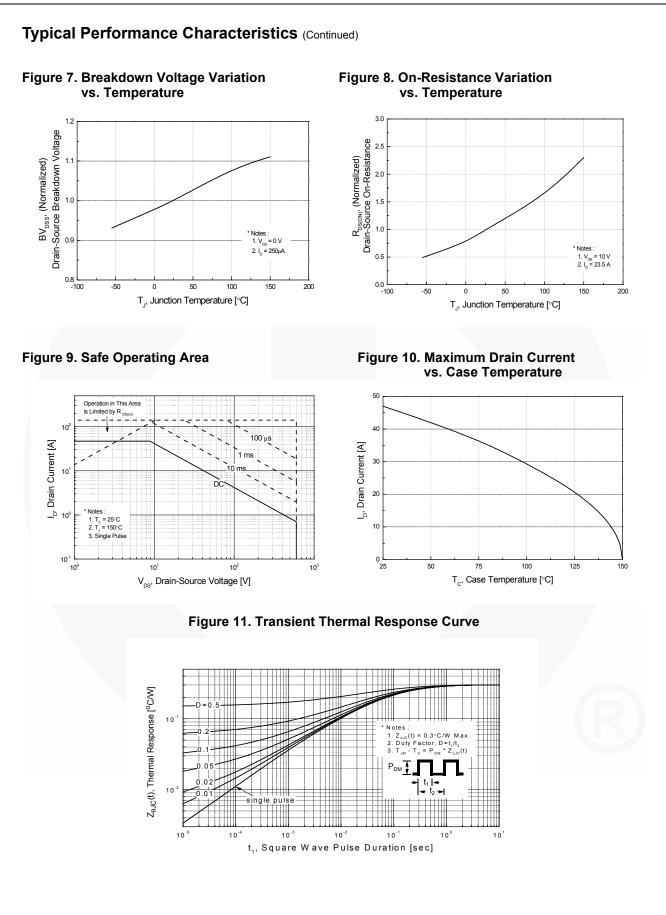
1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. I_{AS} = 18 A, V_{DD} = 50 V, R_{G} = 25 $\Omega,$ starting T_{J} = 25°C.

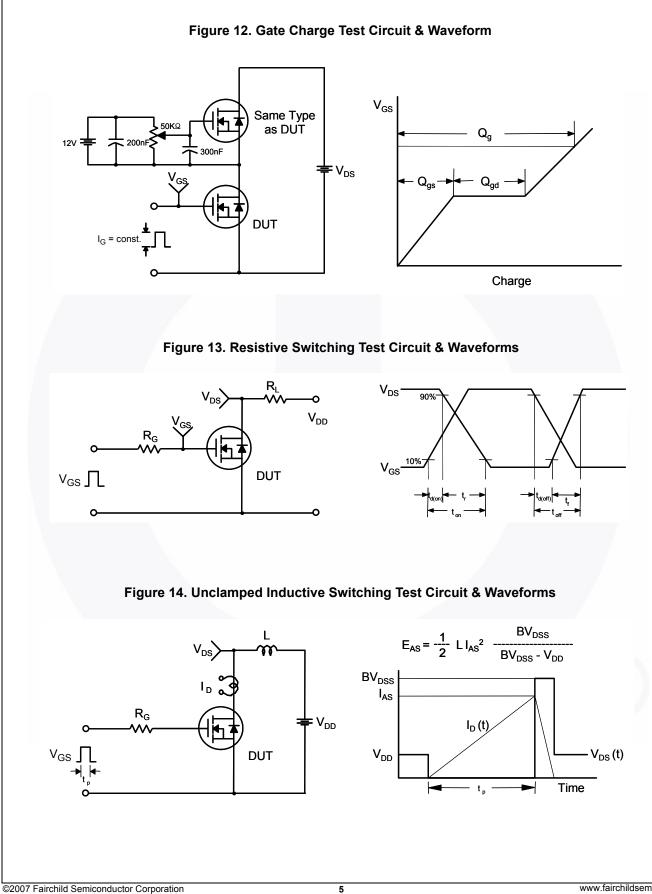
3. I_{SD} \leq 47 A, di/dt \leq 1200 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.

4. Essentially independent of operating temperature typical characteristics.

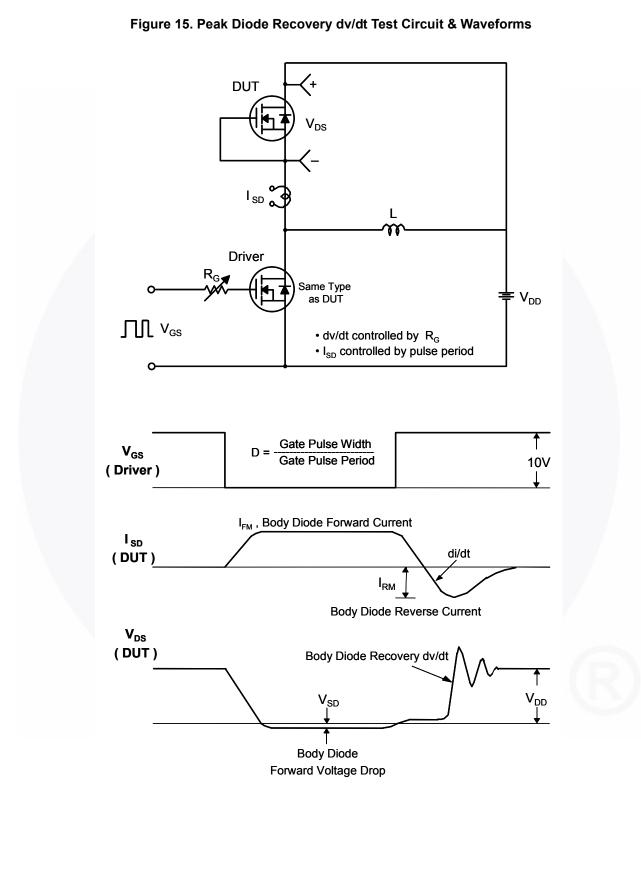


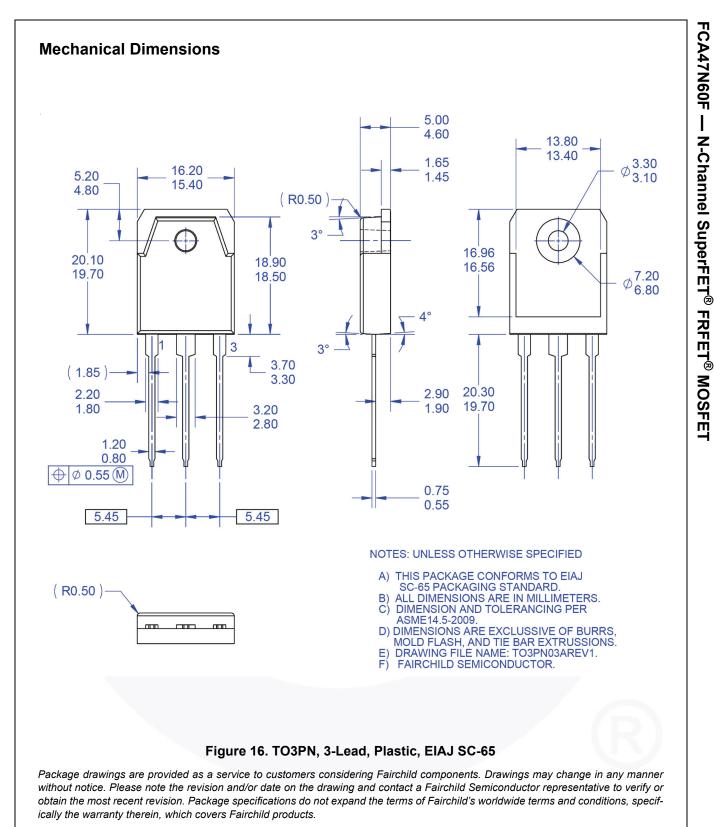


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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT3PN-003



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